Method For Manufacturing A Monocrystalline Layer Of GaAs Material And Substrate For Epitaxial Growth Of A Monocrystalline Layer Of GaAs Material

FIELD OF THE INVENTION

The present invention relates to a process for producing a monocrystalline layer of GaAs material and a substrate for the epitaxial growth of such a monocrystalline layer of GaAs material.

PRIOR ART

Certain materials are not currently available as a monocrystalline substrate in the form of a large-diameter wafer. Moreover, certain materials may be available in large diameter but not with certain characteristics or specifications in terms of quality, in particular with regard to the density of defects or the required electrical or optical properties.

SUMMARY OF THE INVENTION

Embodiments of the present invention aim to overcome these limitations of the prior art by providing a process for producing a monocrystalline layer of GaAs material and a substrate for the epitaxial growth of such a monocrystalline layer of GaAs material. In this way it is possible to address the problem of size of the monocrystalline substrates of GaAs material currently available.

An aspect of the invention provides a process for producing a monocrystalline layer of GaAs material comprising the transfer of a monocrystalline seed layer of $SrTiO_3$ material to a carrier substrate of silicon material followed by epitaxial growth of a monocrystalline layer of GaAs material. The transfer of the monocrystalline seed layer of $SrTiO_3$ material to the carrier substrate of silicon material comprises a step of joining a monocrystalline substrate of $SrTiO_3$ material to the carrier substrate followed by a step of thinning of said monocrystalline substrate of $SrTiO_3$ material.

In advantageous embodiments, the monocrystalline seed layer has a thickness of less than 10 μm, preferably less than 2 μm, and more preferably less than 0.2 μm.

In advantageous embodiments, the thinning step comprises the formation of a weakened zone delimiting a portion of the monocrystalline substrate of $SrTiO_3$ material intended to be transferred to the carrier substrate of silicon material.

In advantageous embodiments, the formation of the weakened zone is obtained by implanting atomic and/or ionic species.

In advantageous embodiments, the thinning step comprises detaching at the weakened zone so as to transfer said portion of the monocrystalline substrate of $SrTiO_3$ material to the carrier substrate of silicon material, in particular the detaching comprises the application of thermal and/or mechanical stress.

In advantageous embodiments, the joining step is a molecular adhesion step.

In advantageous embodiments, the monocrystalline seed layer of $SrTiO_3$ material is in the form of a plurality of tiles each transferred to the carrier substrate of silicon material.

In advantageous embodiments, the carrier substrate of silicon material comprises a detachable interface configured to be detached by means of chemical attack and/or by means of mechanical stress.

There is also disclosed a substrate for epitaxial growth of a monocrystalline layer of GaAs material, characterized in that it comprises a monocrystalline seed layer of $SrTiO_3$ material on a carrier substrate of silicon material.

CLAIMS

1. A process for producing a monocrystalline layer of GaAs material comprising the transfer of a monocrystalline seed layer of $SrTiO_3$ material to a carrier substrate of silicon material followed by epitaxial growth of the monocrystalline layer of GaAs material, wherein the transfer of the monocrystalline seed layer of $SrTiO_3$ material to the carrier substrate of silicon material comprises a step of joining a monocrystalline substrate of $SrTiO_3$ material to the carrier substrate followed by a step of thinning said monocrystalline substrate of $SrTiO_3$ material.

2. The process as claimed in claim 1, wherein the monocrystalline seed layer has a thickness of less than 10 µm, preferably less than 2 µm, and more preferably less than 0.2 µm.

3. The process as claimed in claim 1, wherein the thinning step comprises the formation of a weakened zone delimiting a portion of the monocrystalline substrate of $SrTiO_3$ material intended to be transferred to the carrier substrate of silicon material.

4. The process as claimed in claim 3, wherein the formation of the weakened zone is obtained by implanting atomic and/or ionic species.

5. The process as claimed in claim 3 or 4, wherein the thinning step comprises detaching at the weakened zone so as to transfer said portion of the monocrystalline substrate of $SrTiO_3$ material to the carrier substrate of silicon material, in particular the detaching comprises the application of a thermal and/or mechanical stress.

6. The process as claimed in any one of the preceding claims, wherein the joining step is a molecular adhesion step.

7. The process as claimed in any one of the preceding claims, wherein the monocrystalline seed layer of $SrTiO_3$ material is in the form of a plurality of tiles each transferred to the carrier substrate of silicon material.

8. The process as claimed in any one of the preceding claims, wherein the carrier substrate of silicon material comprises a detachable interface configured to be detached by means of chemical attack and/or by means of mechanical stress.